

FIG.1A

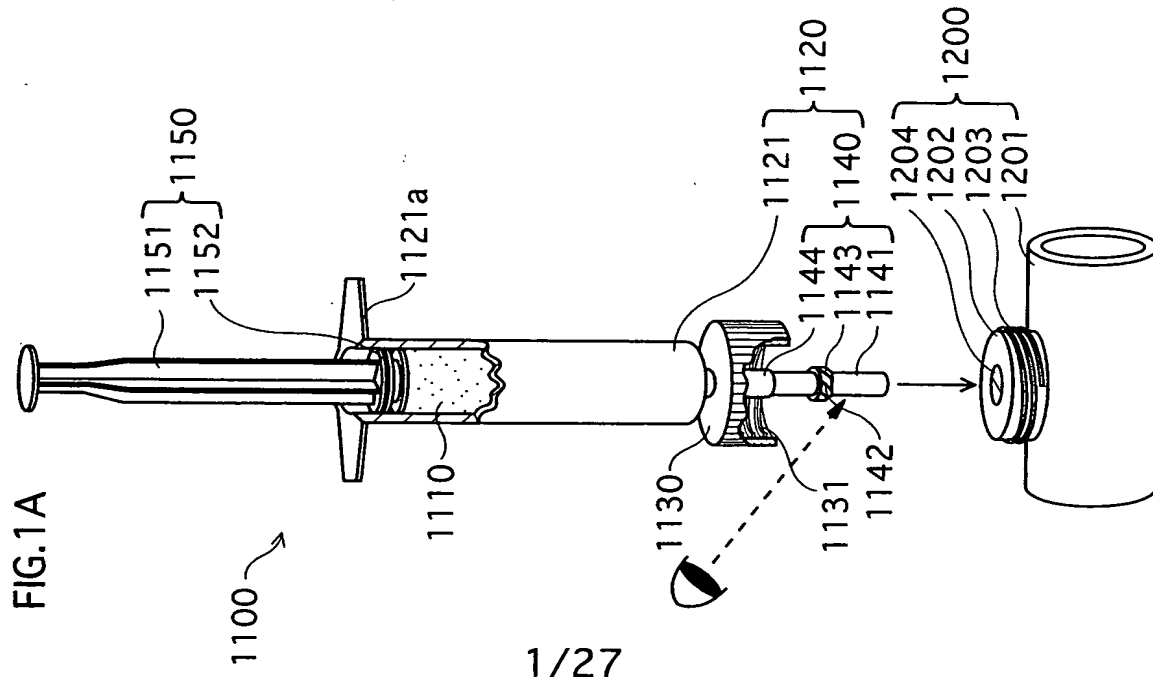


FIG.1B

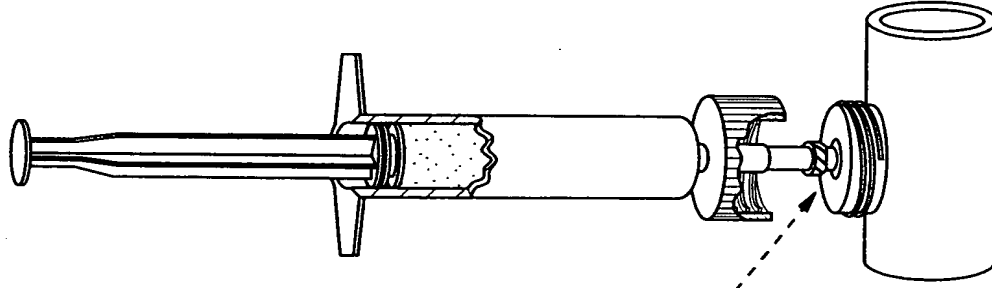


FIG.1C

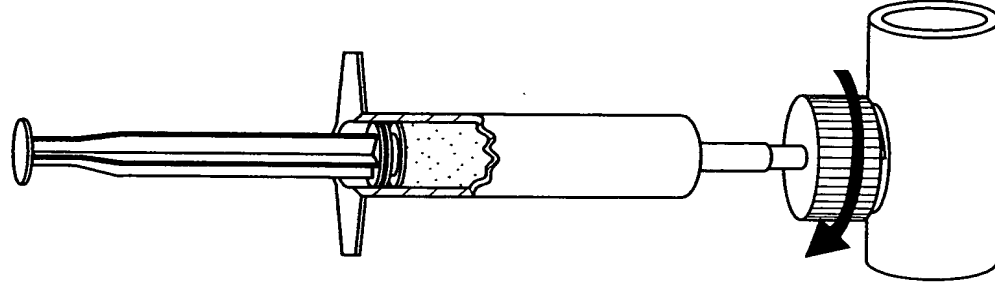


FIG.2A

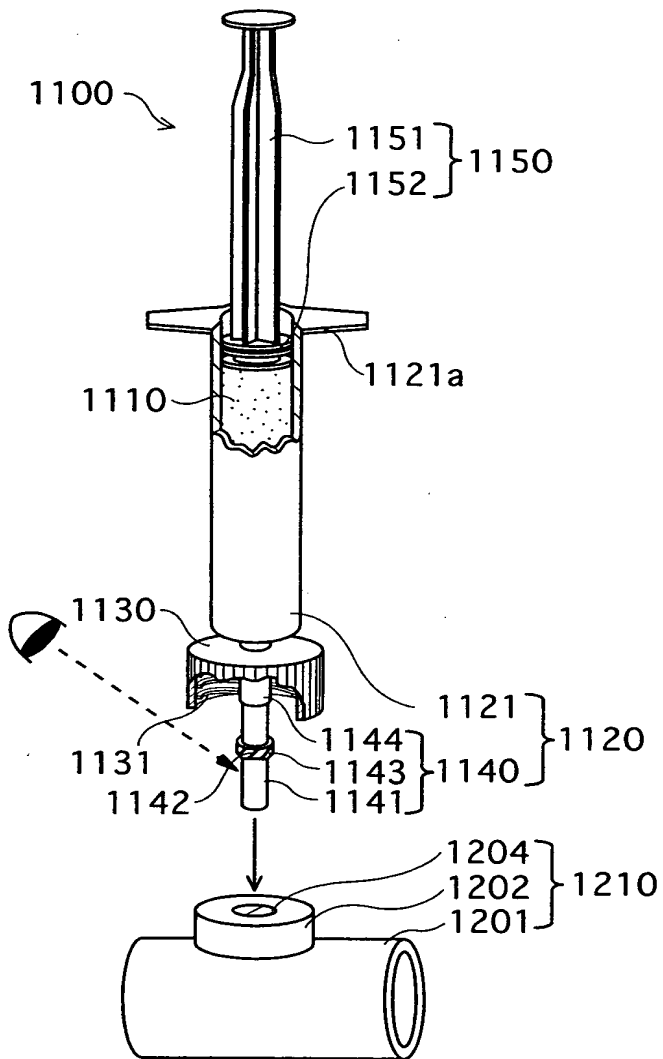


FIG.2B

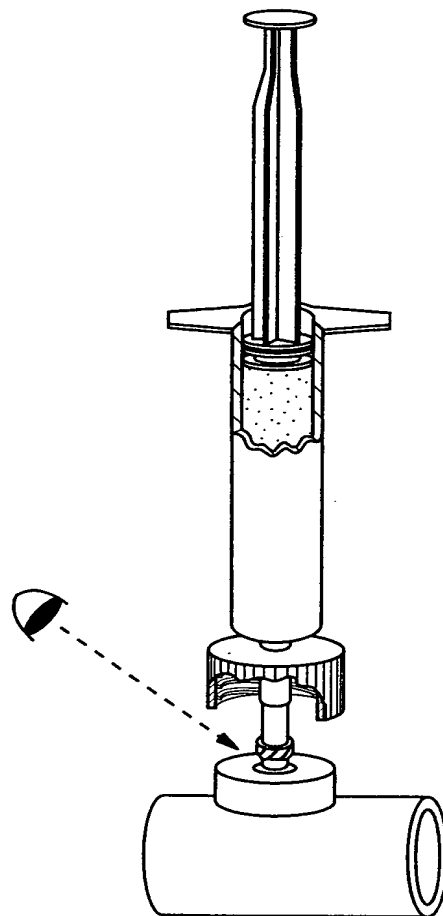


FIG.3A

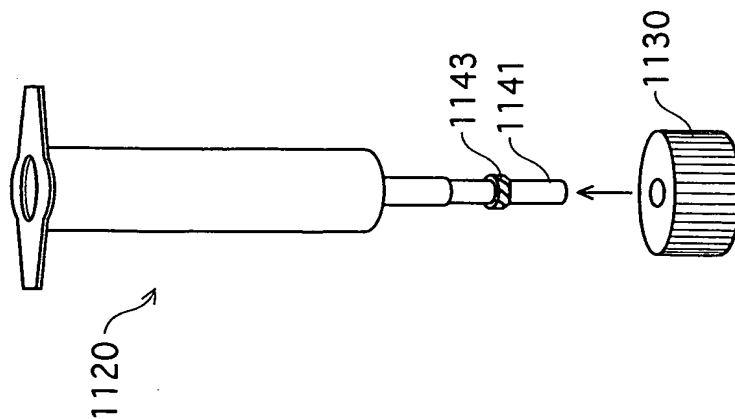


FIG.3B

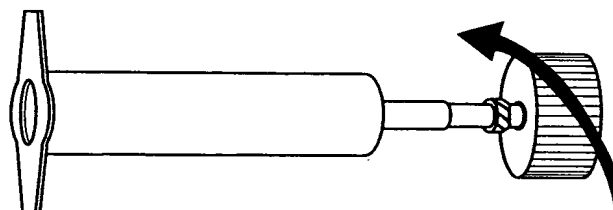


FIG.3C

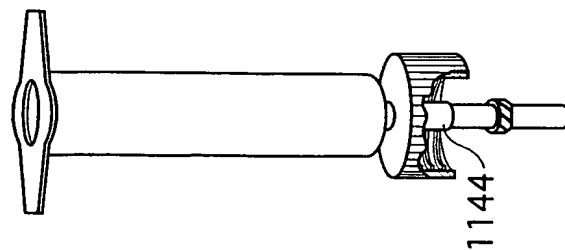


FIG.4

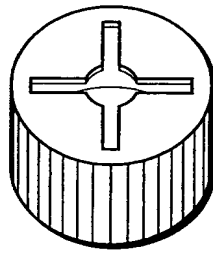


FIG.5A

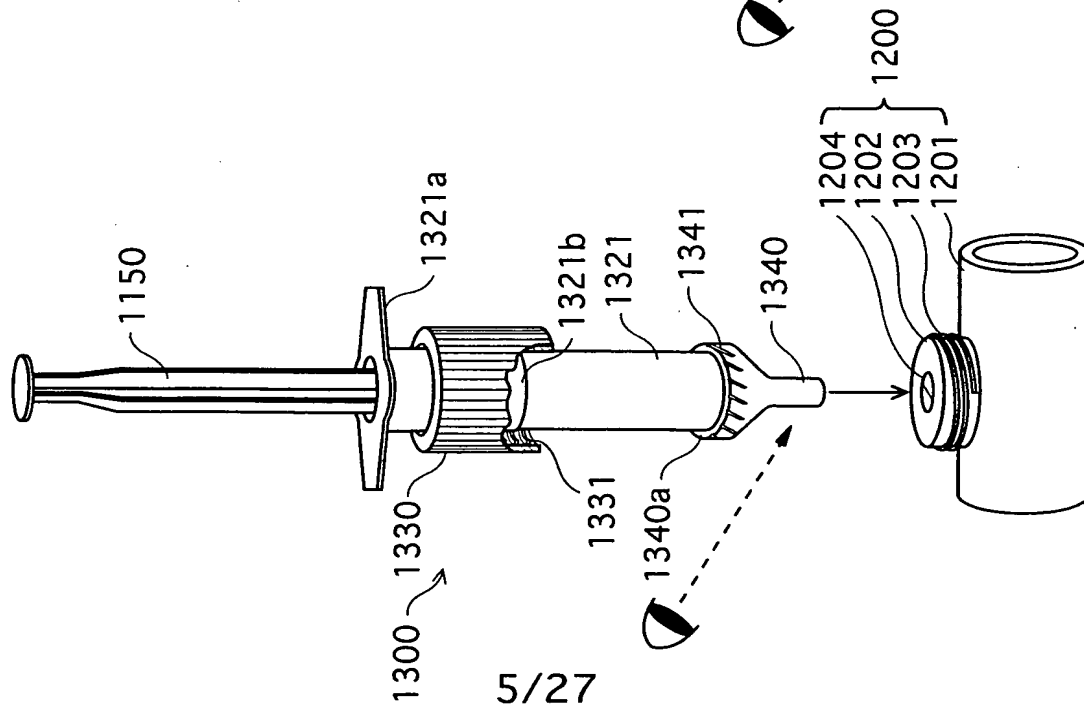


FIG.5B

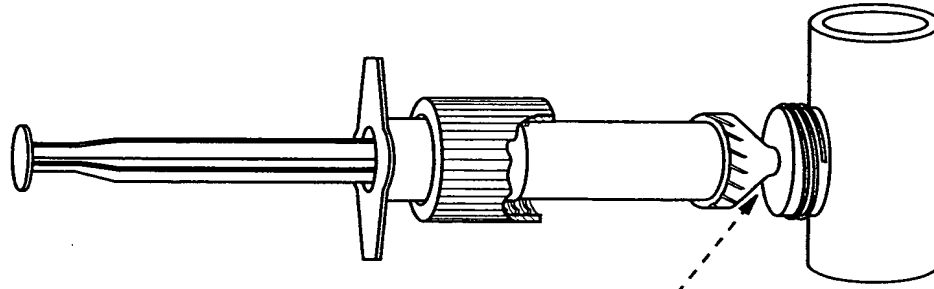


FIG.5C

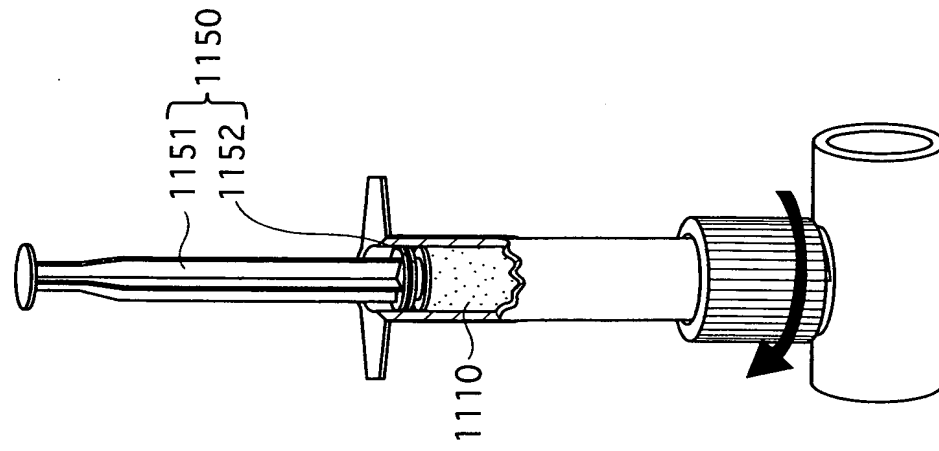


FIG.6A

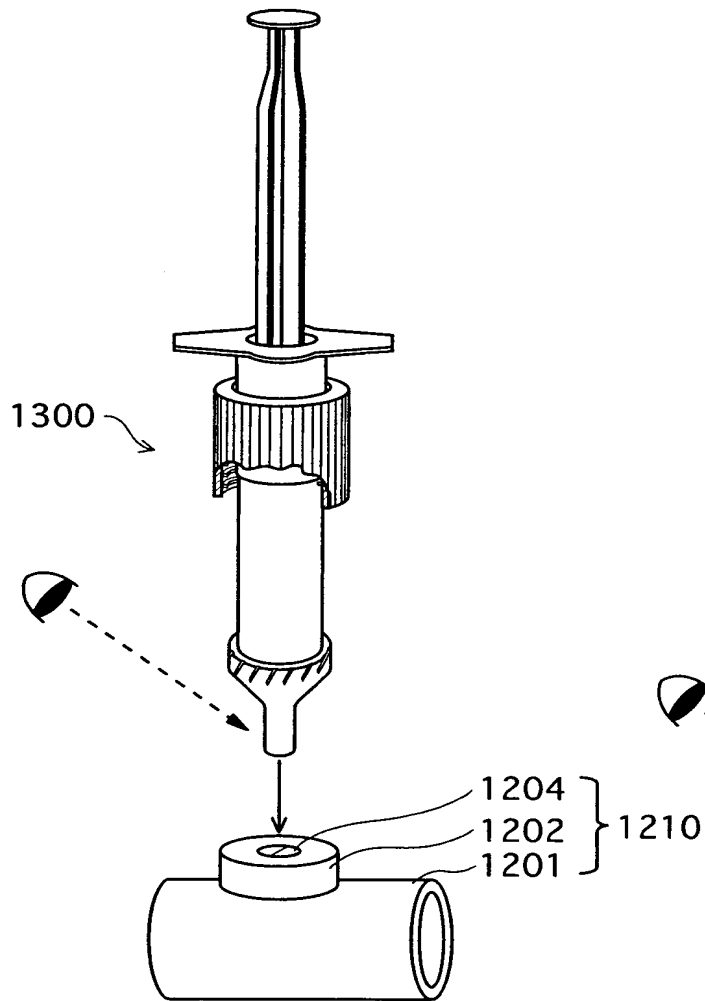


FIG.6B

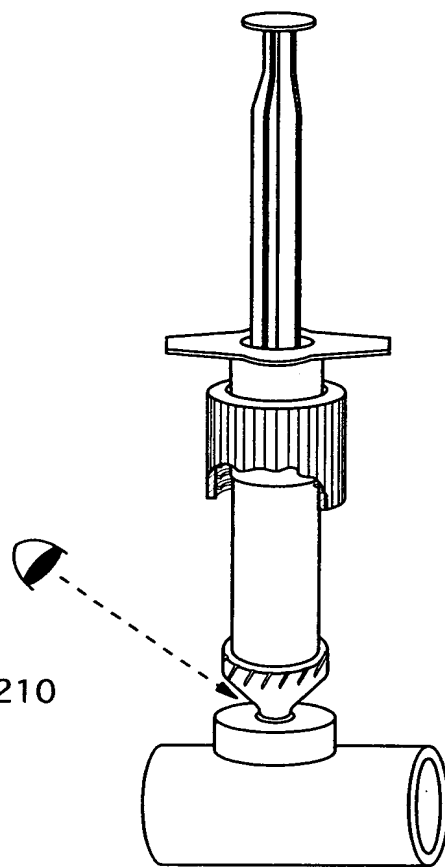


FIG.7

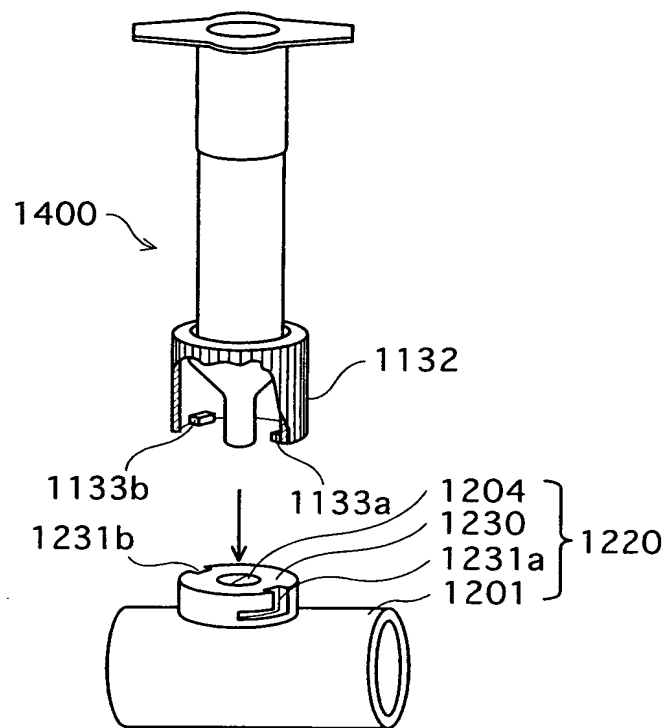


FIG.8A

(a)

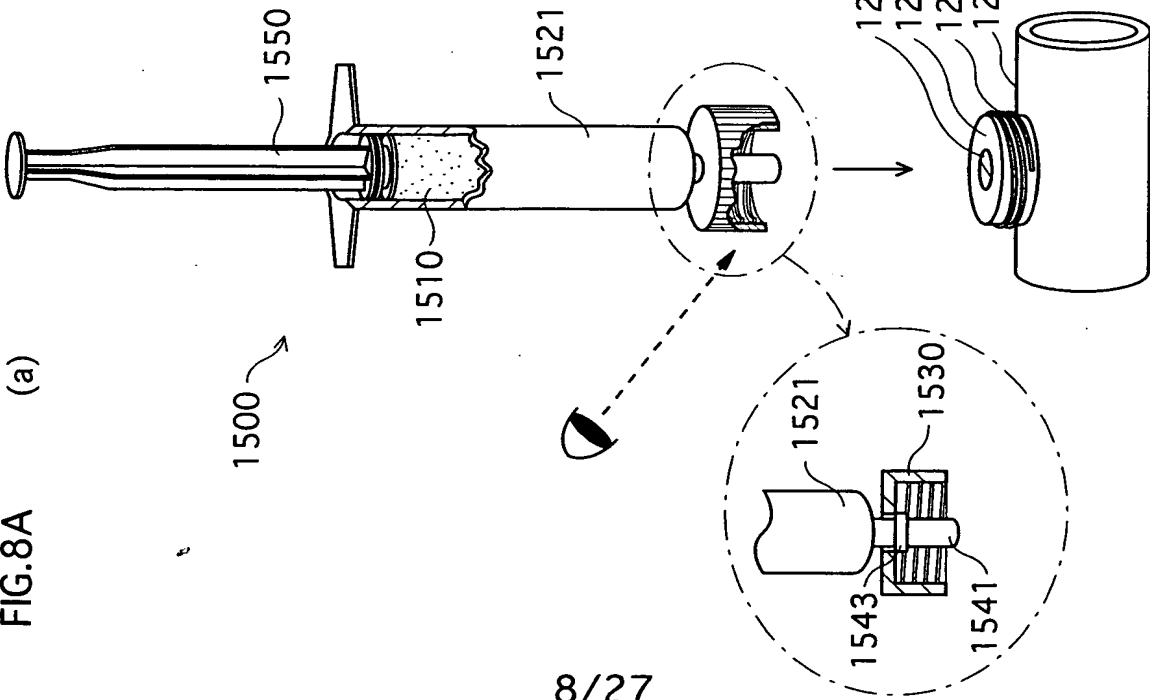


FIG.8B

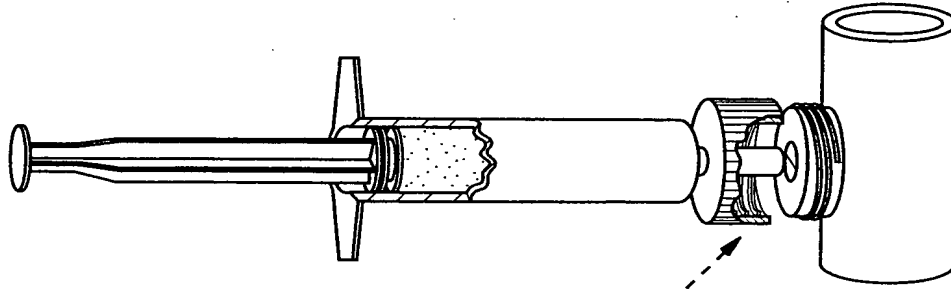


FIG.8C

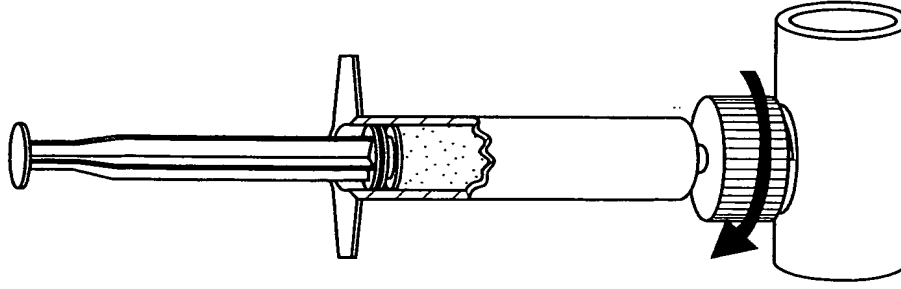




FIG.9A

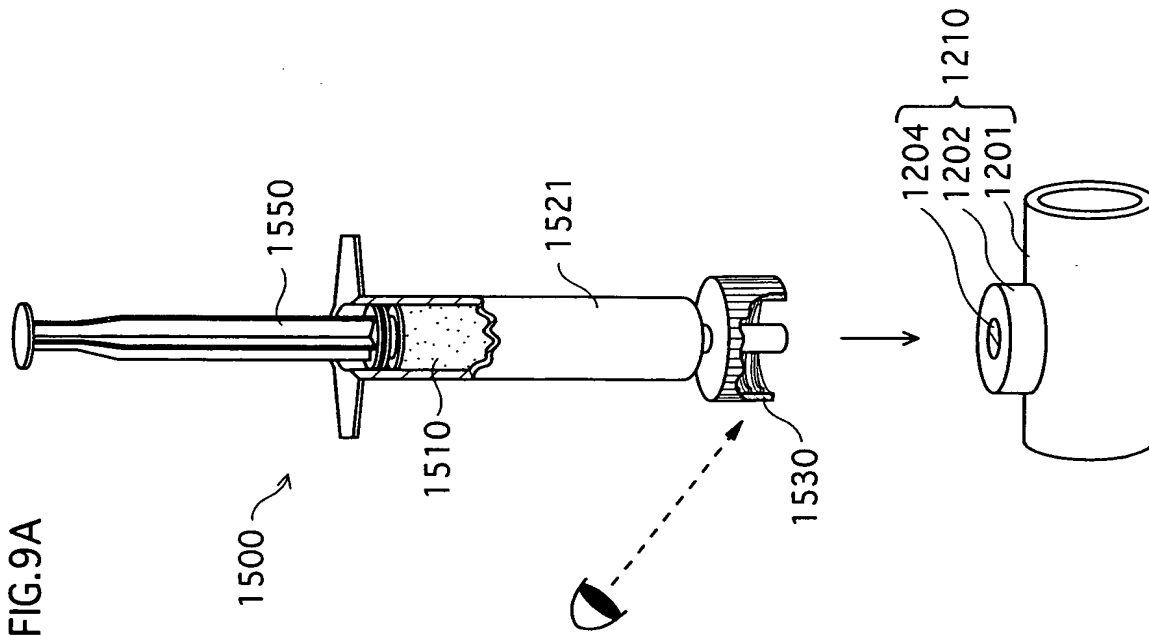


FIG.9B

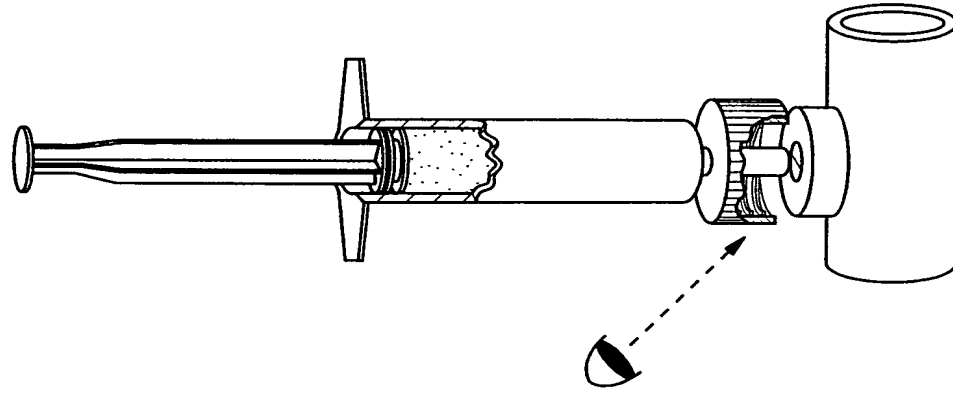


FIG.9C

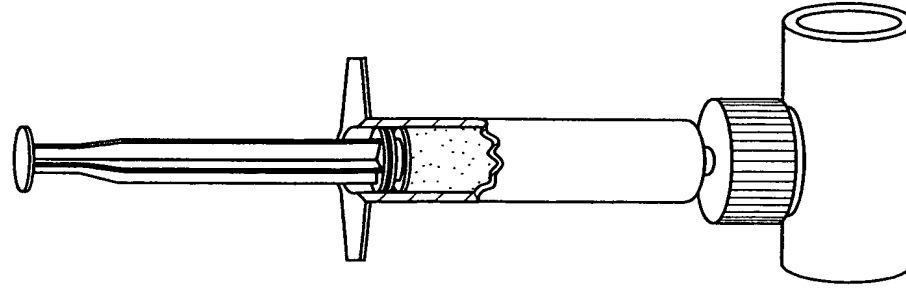


FIG.10A

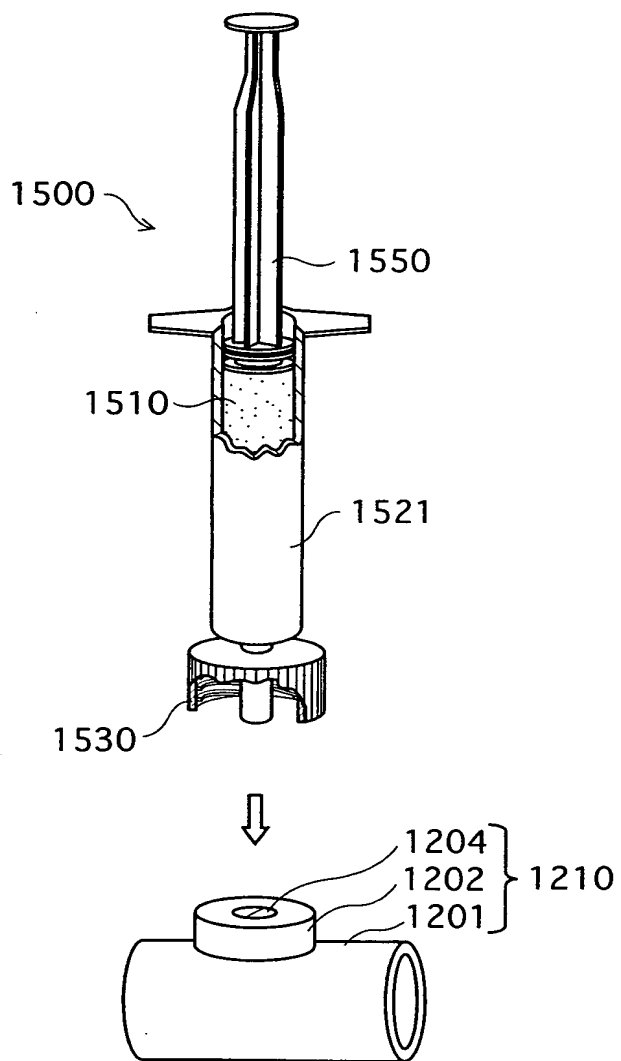


FIG.10B

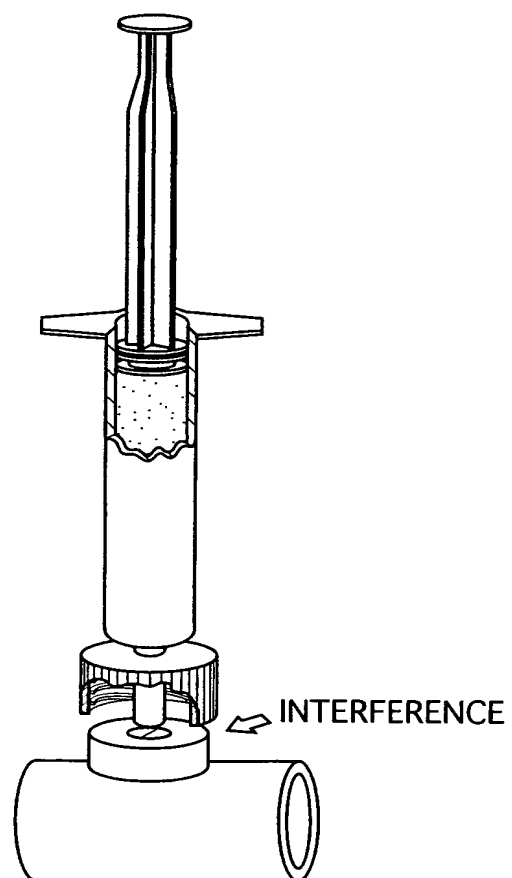


FIG.11A

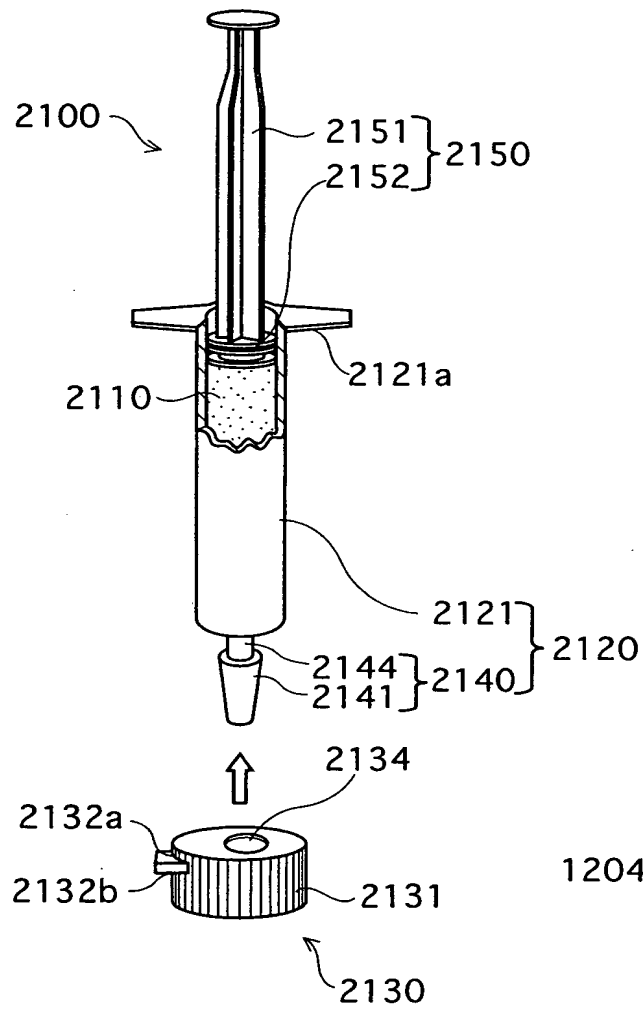


FIG.11B

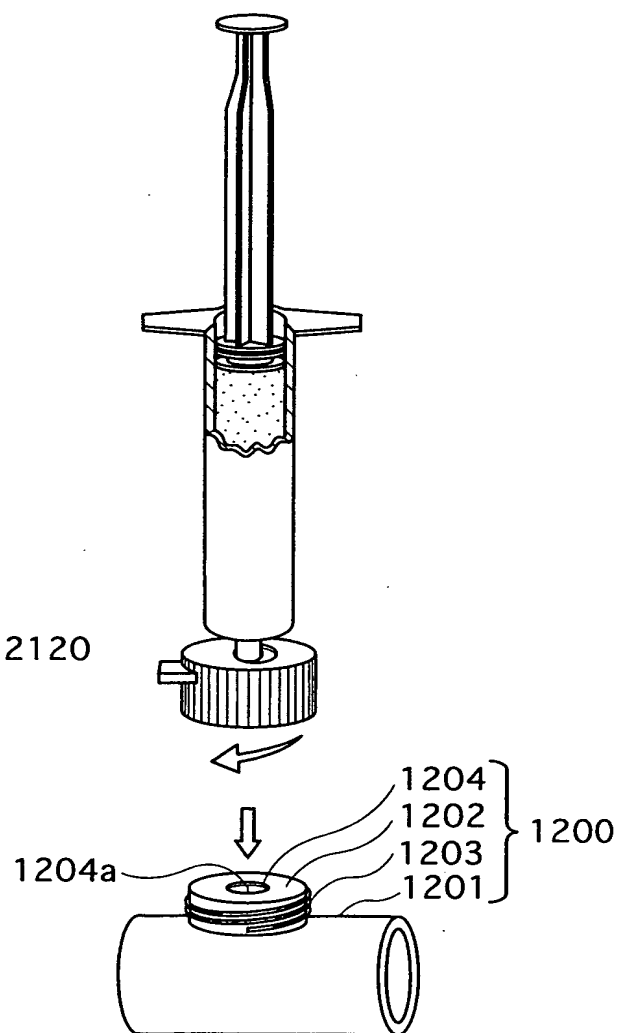


FIG.12A

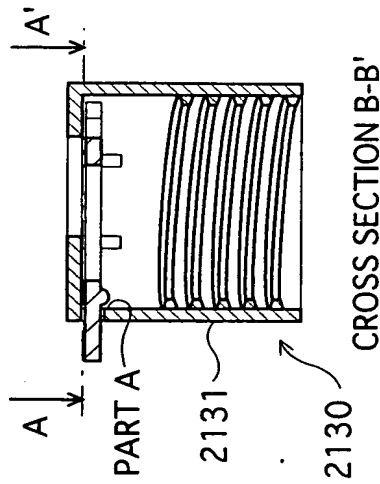


FIG.12B

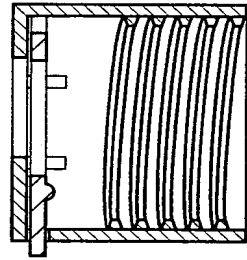


FIG.12C

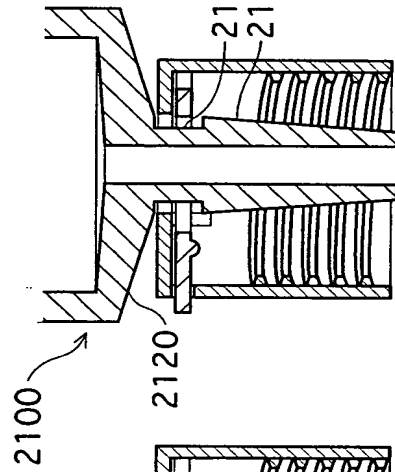


FIG.12D

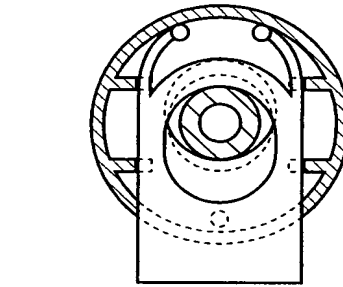
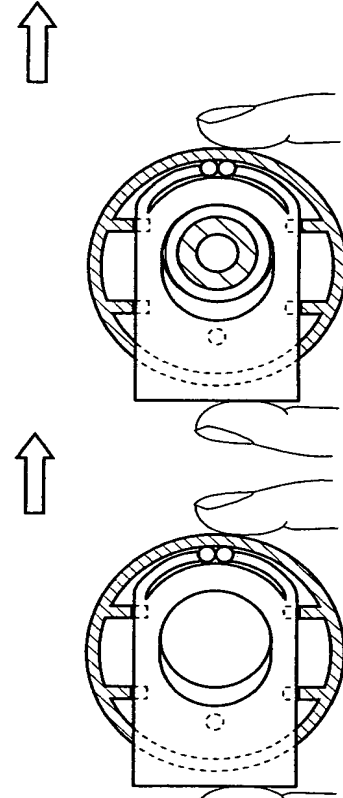
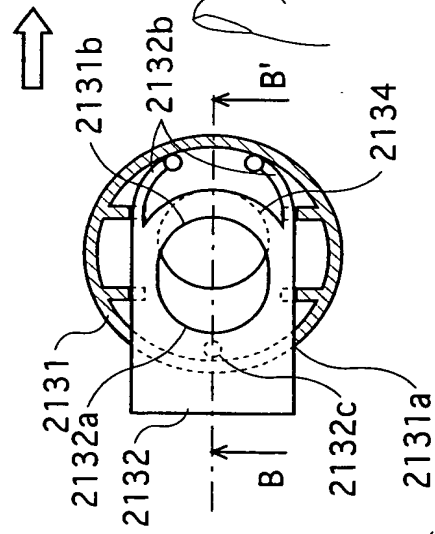
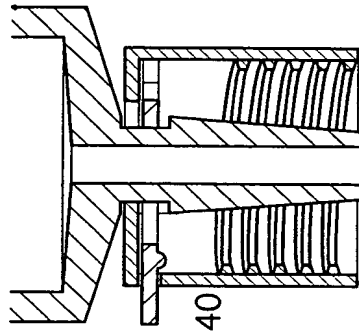


FIG.13

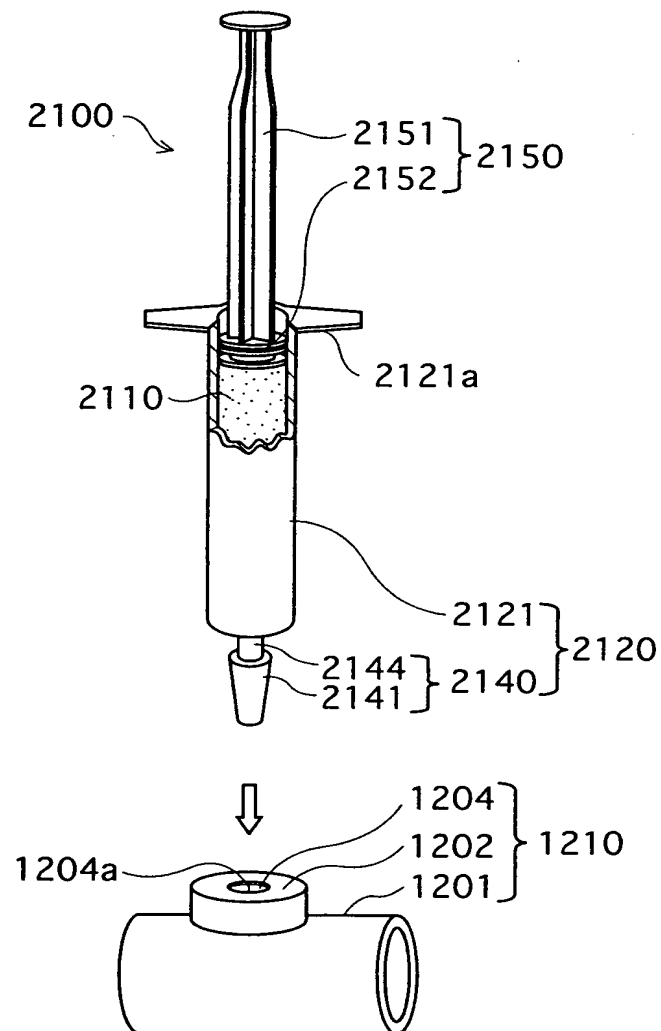
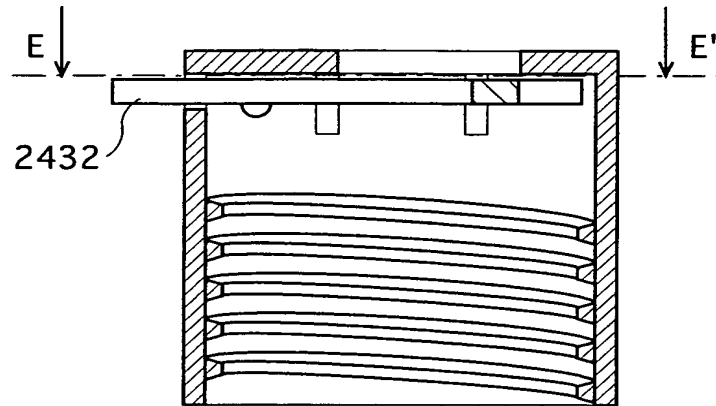
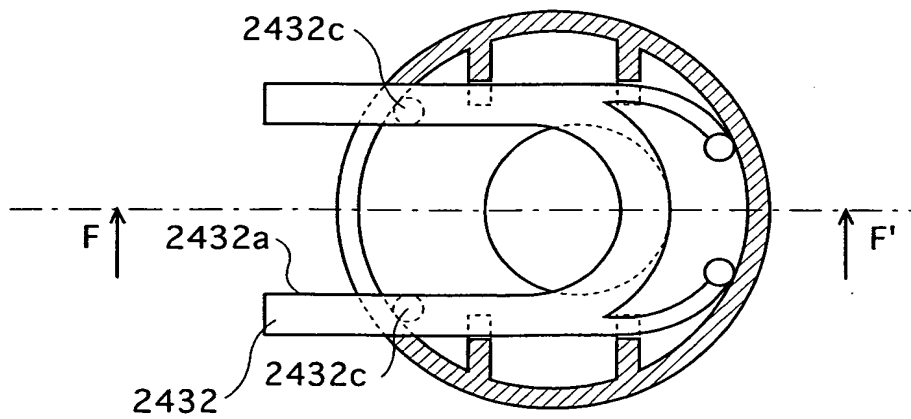


FIG.14

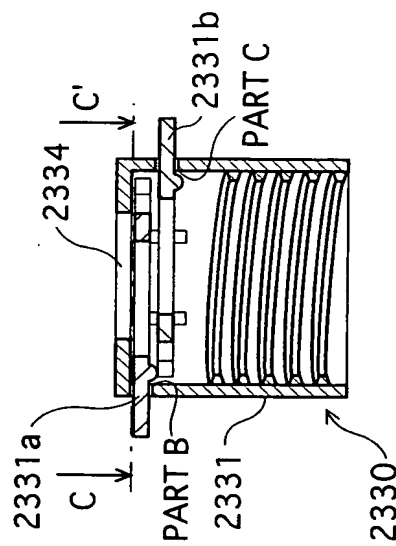


CROSS SECTION F-F'

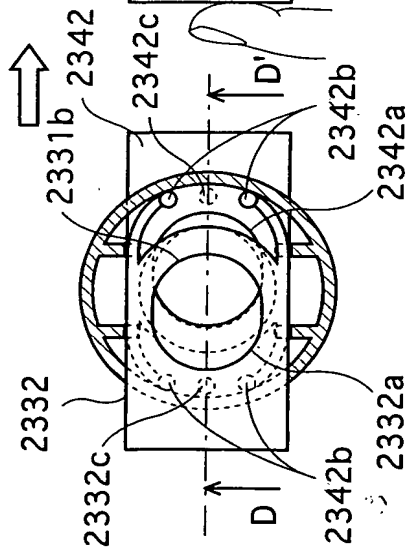


CROSS SECTION E-E'

FIG.15A



CROSS SECTION D-D'



CROSS SECTION C-C'

FIG.15B

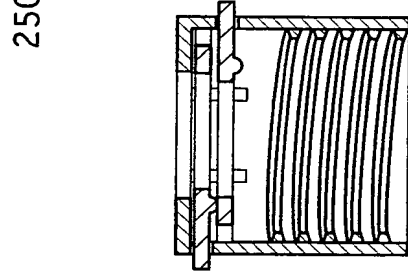


FIG.15C

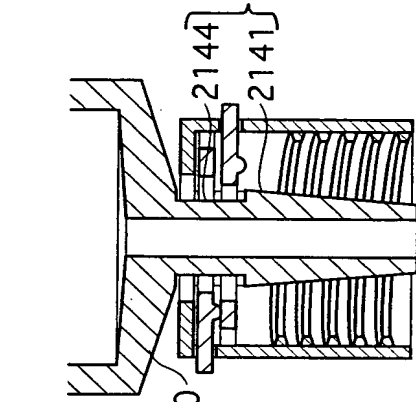


FIG.15D

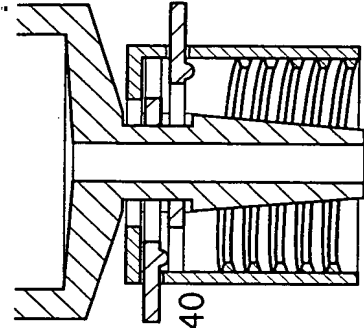
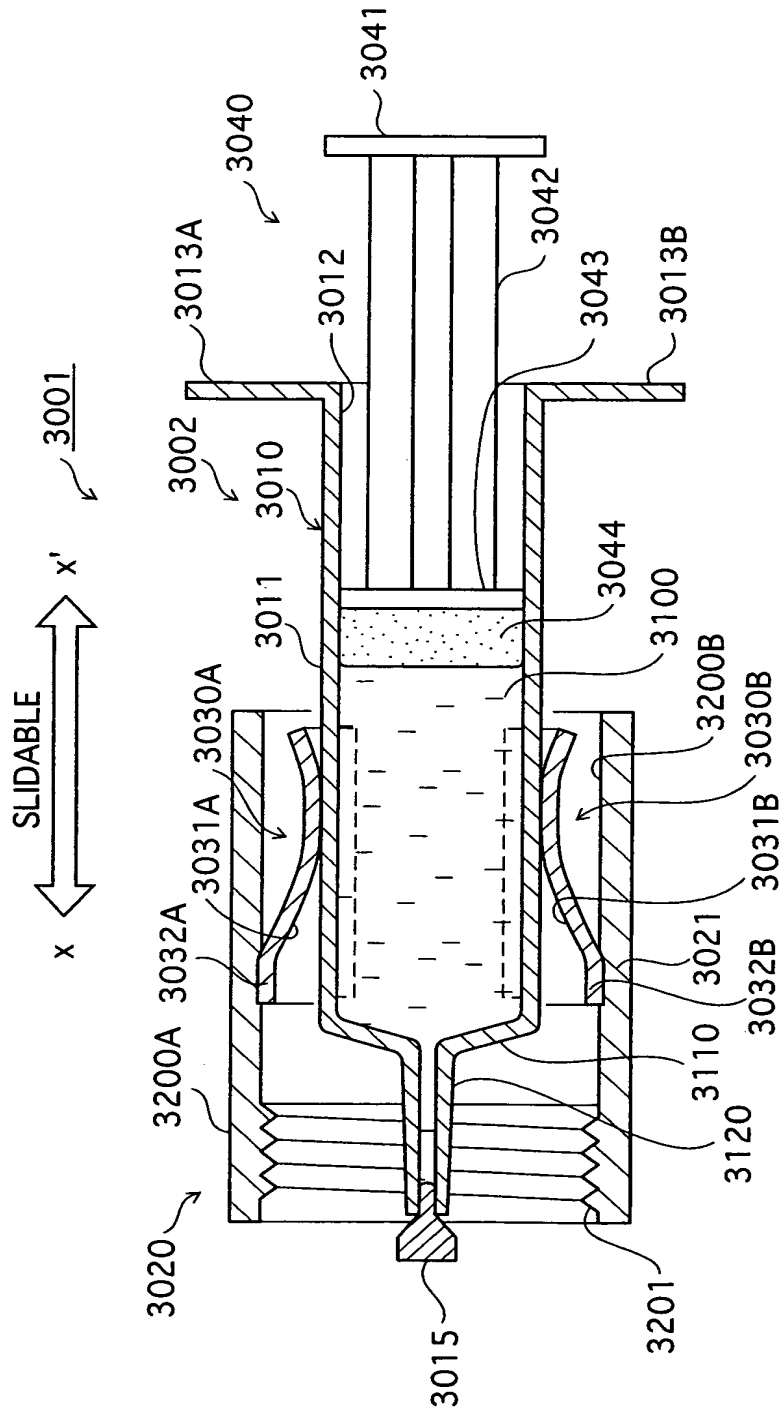


FIG.16





[illegible]

[illegible]

FIG. 19

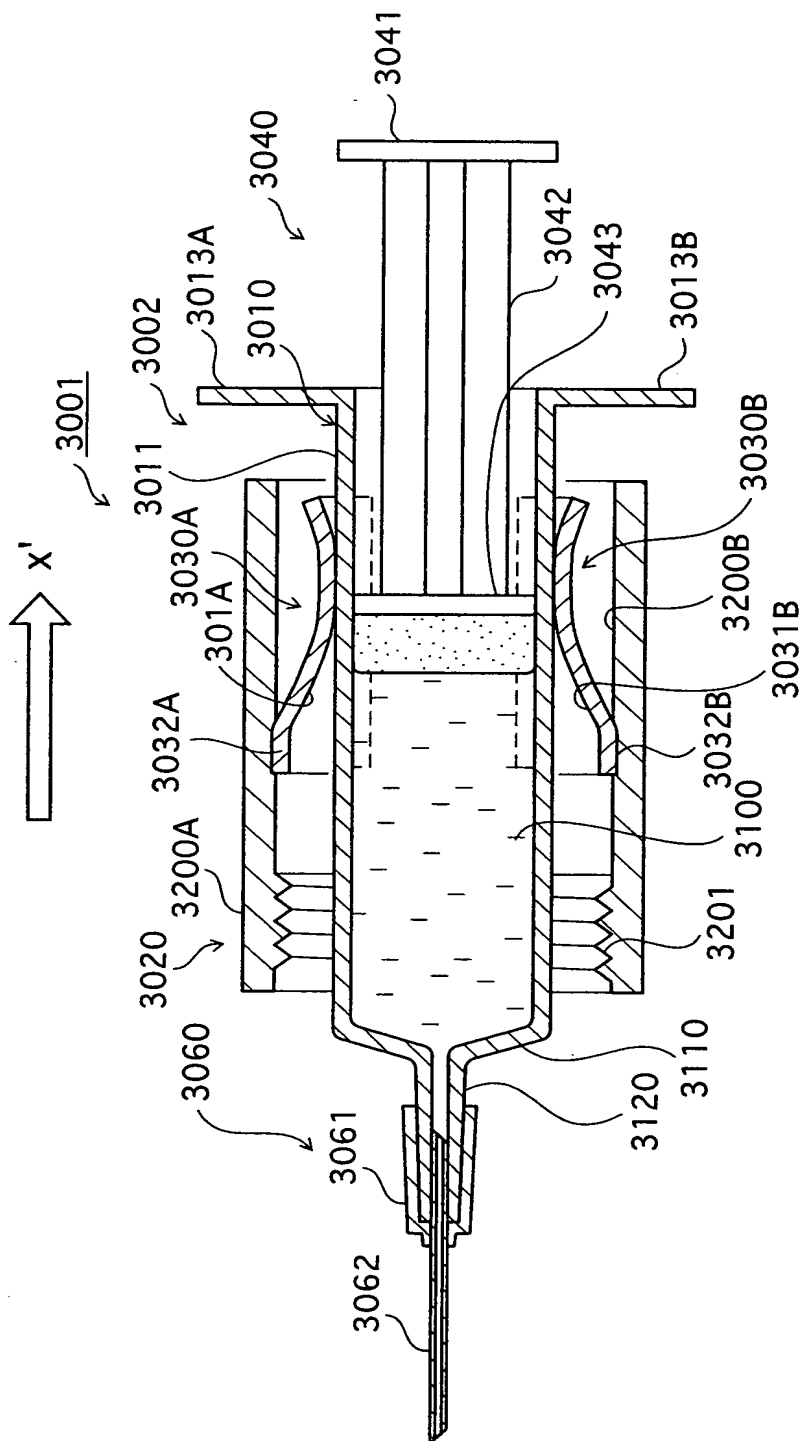
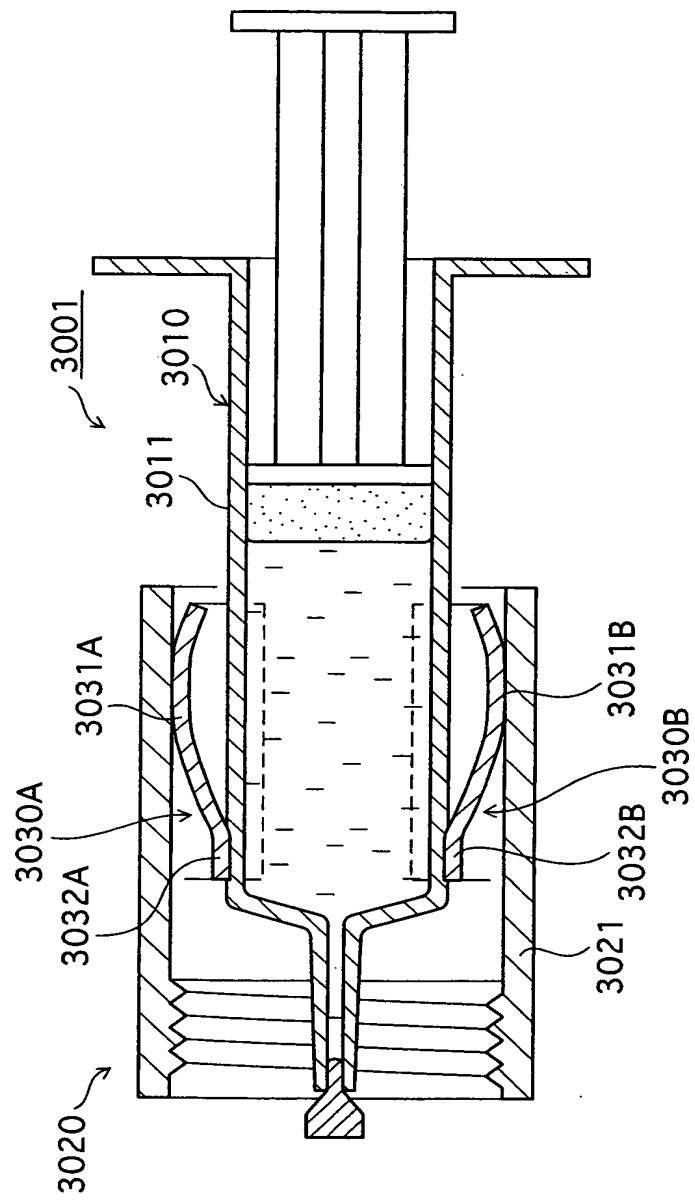


FIG.20



This cross-sectional view shows the device 3001 along the X-axis. It features a substrate 3050 with a top layer 3020. A central region 3010 is defined by side walls 3011 and 3013A. A top layer 3040 covers the central region, with a central portion 3041 and side portions 3042, 3043, and 3044. A bottom layer 3030 is located beneath the central region, with a central portion 3036 and side portions 3035 and 3037. A central region 3100 is defined by side walls 3110 and 3120. A top layer 3200B is located above the central region, with a central portion 3200A and side portions 3201 and 3202. A bottom layer 3052 is located beneath the central region, with a central portion 3055 and side portions 3056 and 3057. A central region 3010 is defined by side walls 3011 and 3013A. A top layer 3040 covers the central region, with a central portion 3041 and side portions 3042, 3043, and 3044. A bottom layer 3030 is located beneath the central region, with a central portion 3036 and side portions 3035 and 3037. A central region 3100 is defined by side walls 3110 and 3120. A top layer 3200B is located above the central region, with a central portion 3200A and side portions 3201 and 3202. A bottom layer 3052 is located beneath the central region, with a central portion 3055 and side portions 3056 and 3057.

This cross-sectional diagram illustrates the internal structure of the device along the X' axis. The central core consists of a substrate 3001 topped by a layer 3002. A central channel or well 3010 is formed within this layer, containing a material 3011. On either side of the center are regions 3013A and 3013B, which are part of a larger structure 3040. Above these regions are layers 3041 and 3042, separated by a boundary 3043. Below the main body, there are additional layers 3044 and 3045. At the bottom, two contact pads 3052 are shown, each containing a material 3051. The entire device is supported by a base 3500.

FIG.23

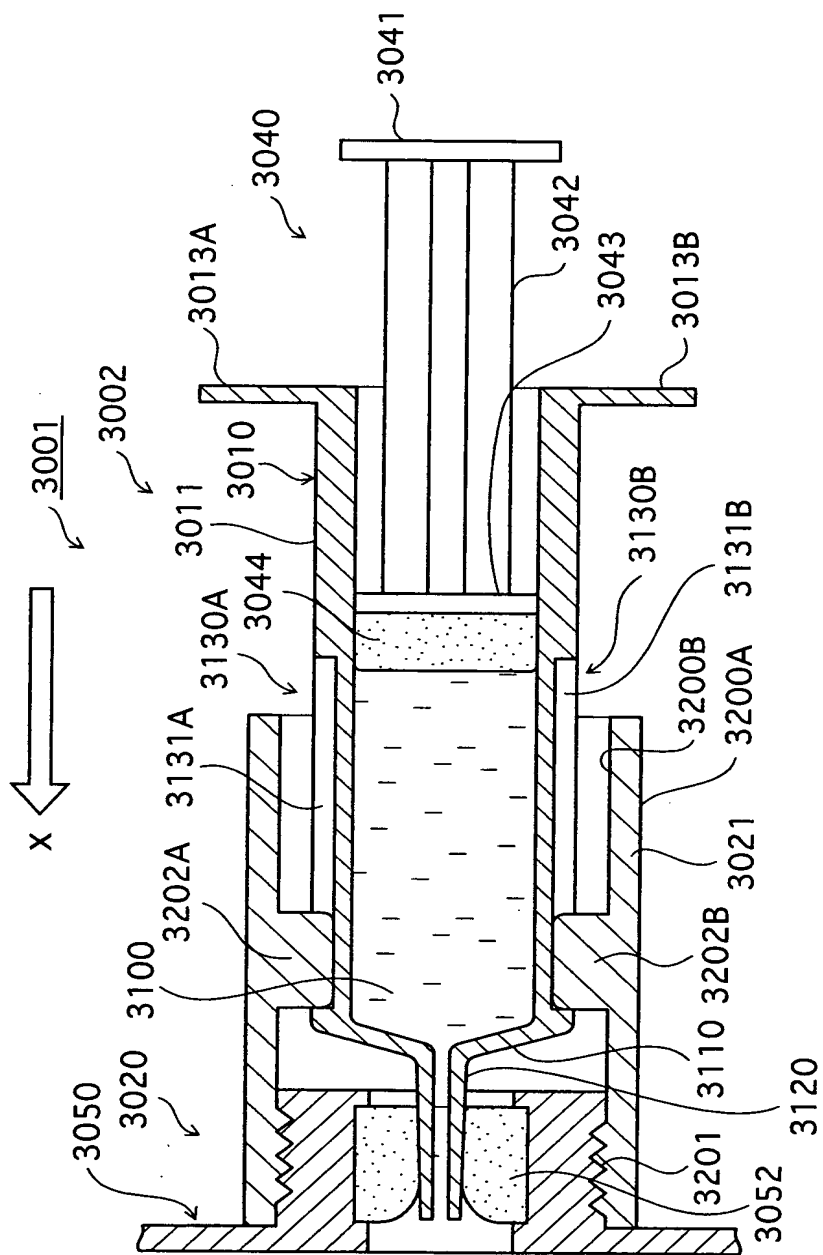


FIG.24

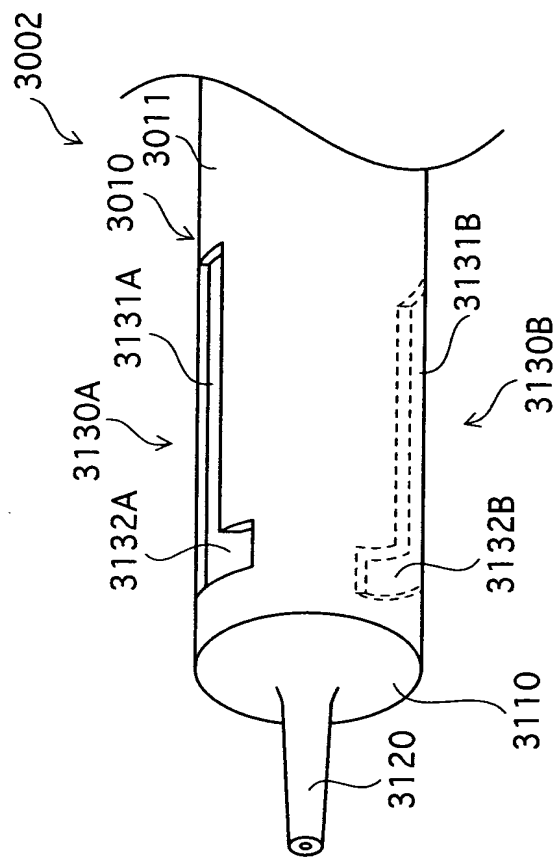




FIG.25

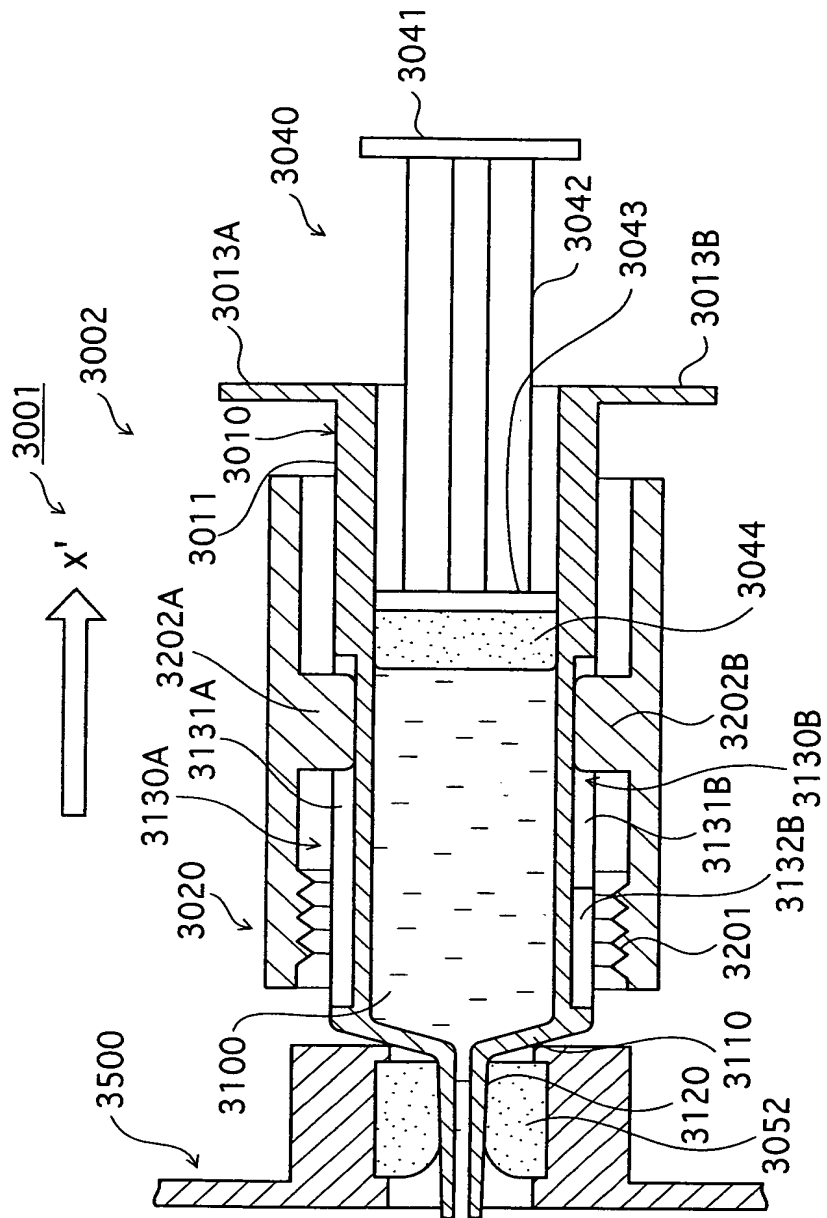


FIG.26A

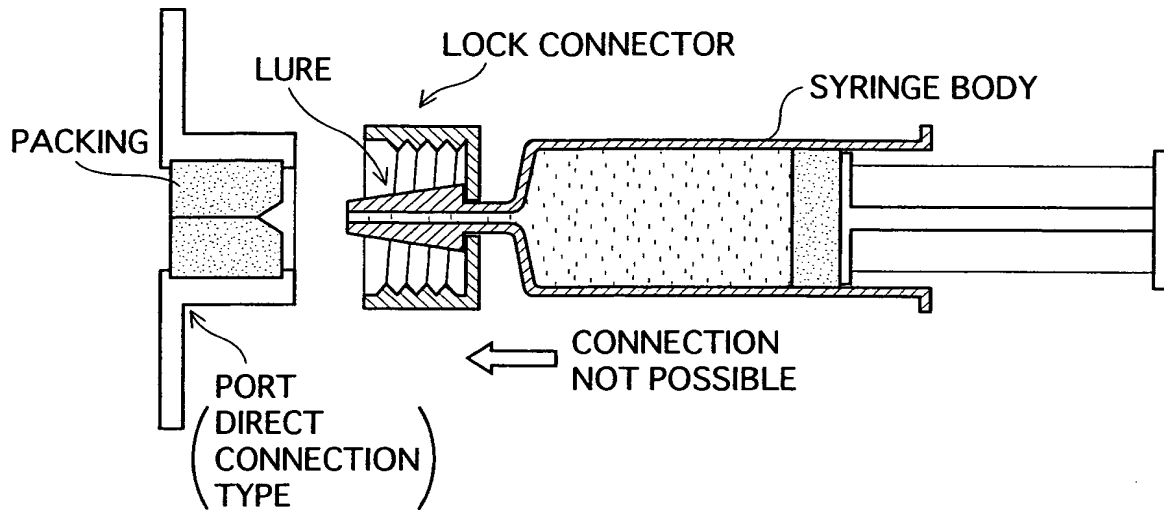


FIG.26B

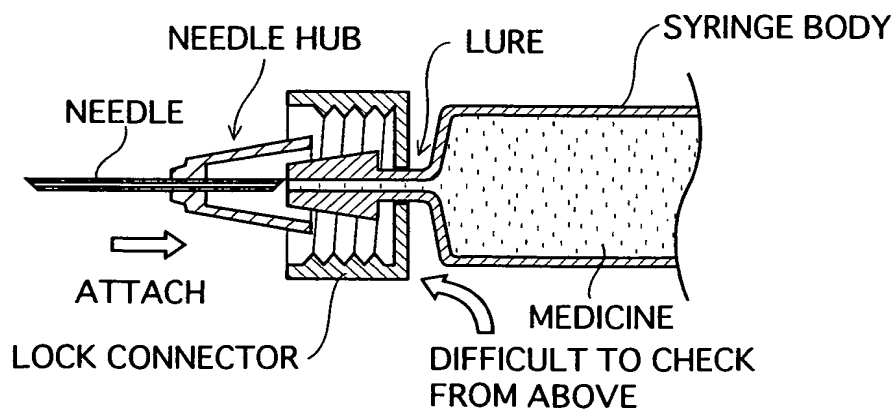


FIG.27A

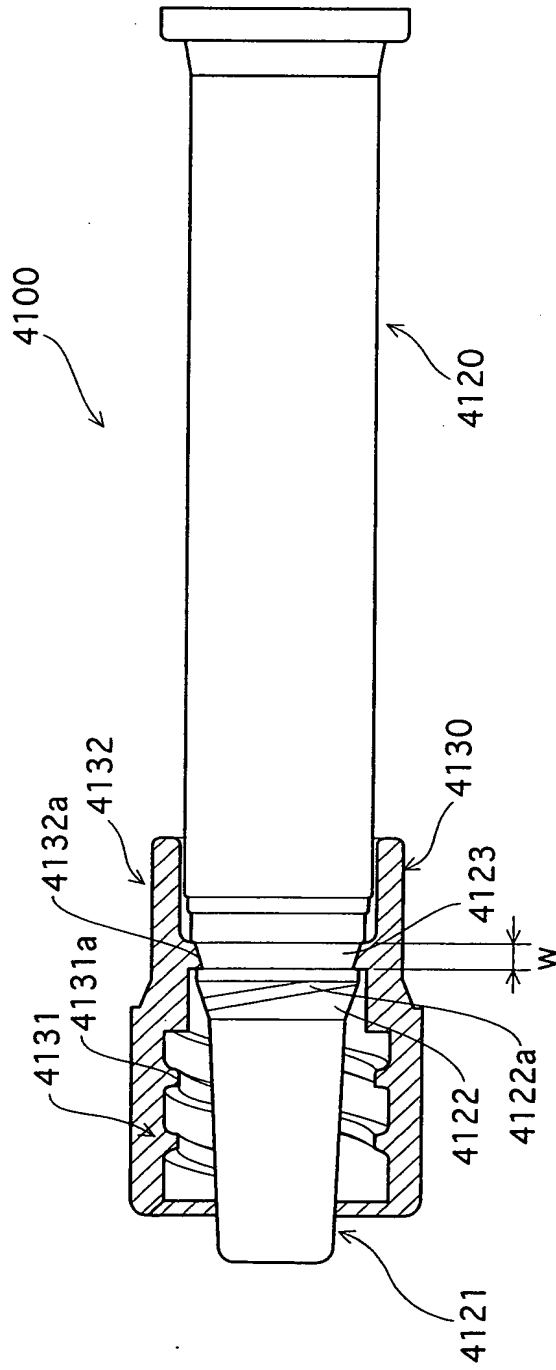


FIG.27B

